

**B. B. Dumre, N. J. Szymanski, V. Adhikari, I. Khatri, D. Gall, S. V. Khare, Solar Energy 194, 742, Supplementary Material (2019)**

## **Improved optoelectronic properties in CdTe<sub>1-x</sub>Se<sub>x</sub> through controlled composition and short-range order**

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### **Supplementary Material**

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**Table S1:** Equilibrium lattice constants (in-plane  $a$  and out-of-plane  $c$ ) of disordered  $\text{CdTe}_{1-x}\text{Se}_x$  in the zincblende and wurtzite structures, computed within the framework of GGA. Experimental data, where available, is listed in parenthesis for comparison.

Material	Zincblende	Wurtzite			
	$x$	$a$ (Å)	$a$ (Å)	$c$ (Å)	$c/a$
0.00	6.624 (6.48 <sup>a</sup> , 6.54 <sup>b</sup> )	4.681 (4.57 <sup>c</sup> )	7.668 (7.47 <sup>c</sup> )	1.638	
0.25	6.521	4.609	7.544	1.637	
0.50	6.418	4.537	7.419	1.635	
0.75	6.311	4.459	7.295	1.636	
1.00	6.207 (6.052 <sup>d</sup> , 6.084 <sup>a</sup> )	4.391 (4.30 <sup>e</sup> )	7.166 (7.02 <sup>e</sup> )	1.632	

a Ref. [108]

b Ref. [14]

c Ref. [109]

d Ref. [110]

e Ref. [111]

**Table S2:** Electronic band gaps of zincblende and wurtzite CdSe<sub>x</sub>Te<sub>1-x</sub> computed using GGA and hybrid HSE06 functionals. Experimental data, where available, is listed in parentheses for comparison.

Material	Band Gap(eV)	
$x$	Wurtzite	Zinc Blende
0.00	0.56 <sup>a</sup> , 1.23 <sup>b</sup> (1.59 <sup>c</sup> )	0.94 <sup>a</sup> , 1.54 <sup>b</sup> (1.50 <sup>d</sup> )
0.25	0.84 <sup>a</sup> , 1.08 <sup>b</sup>	0.86 <sup>a</sup> , 1.45 <sup>b</sup>
0.50	0.76 <sup>a</sup> , 1.01 <sup>b</sup>	0.81 <sup>a</sup> , 1.42 <sup>b</sup>
0.75	0.77 <sup>a</sup> , 1.05 <sup>b</sup>	0.85 <sup>a</sup> , 1.46 <sup>b</sup>
1.00	1.06 <sup>a</sup> , 1.32 <sup>b</sup> (1.70 <sup>e</sup> )	1.03 <sup>a</sup> , 1.61 <sup>b</sup> (1.78 <sup>f</sup> )

<sup>a</sup> This work using GGA

<sup>b</sup> This work using HSEO6

<sup>c</sup> Ref. [94]

<sup>d</sup> Ref [20]

<sup>e</sup> Ref. [19]

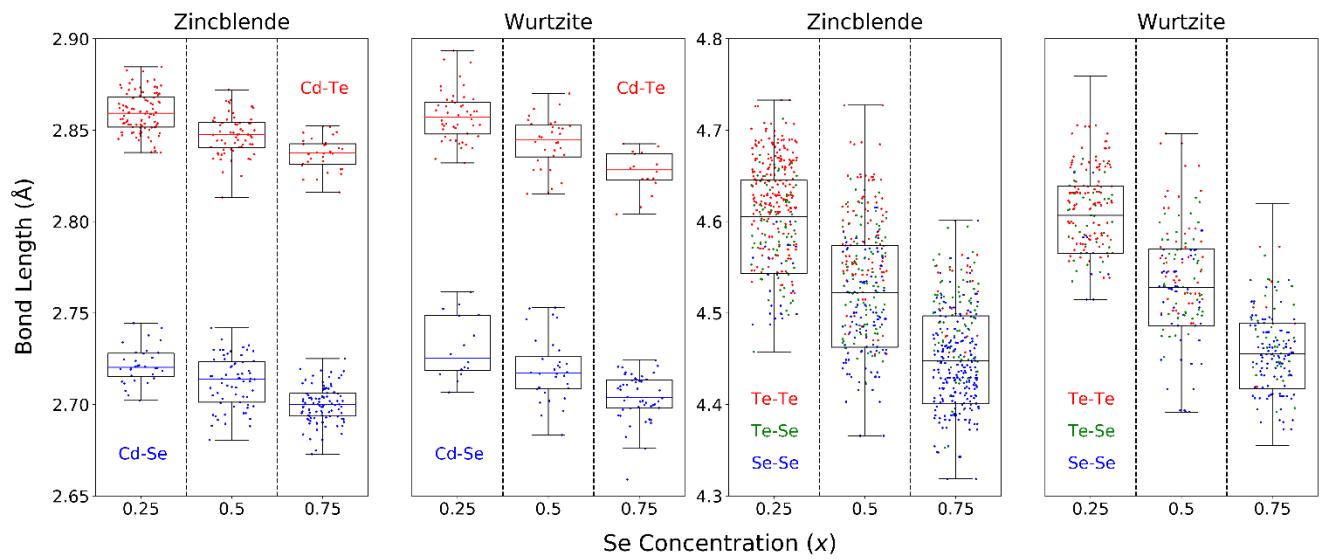
<sup>f</sup> Ref. [93]

**Table S3:** Charge transfer (in elementary charge units  $e$ ) from Cd to Te and Se in  $\text{CdSe}_x\text{Te}_{1-x}$  calculated using the Bader charge partitioning scheme [77-80].

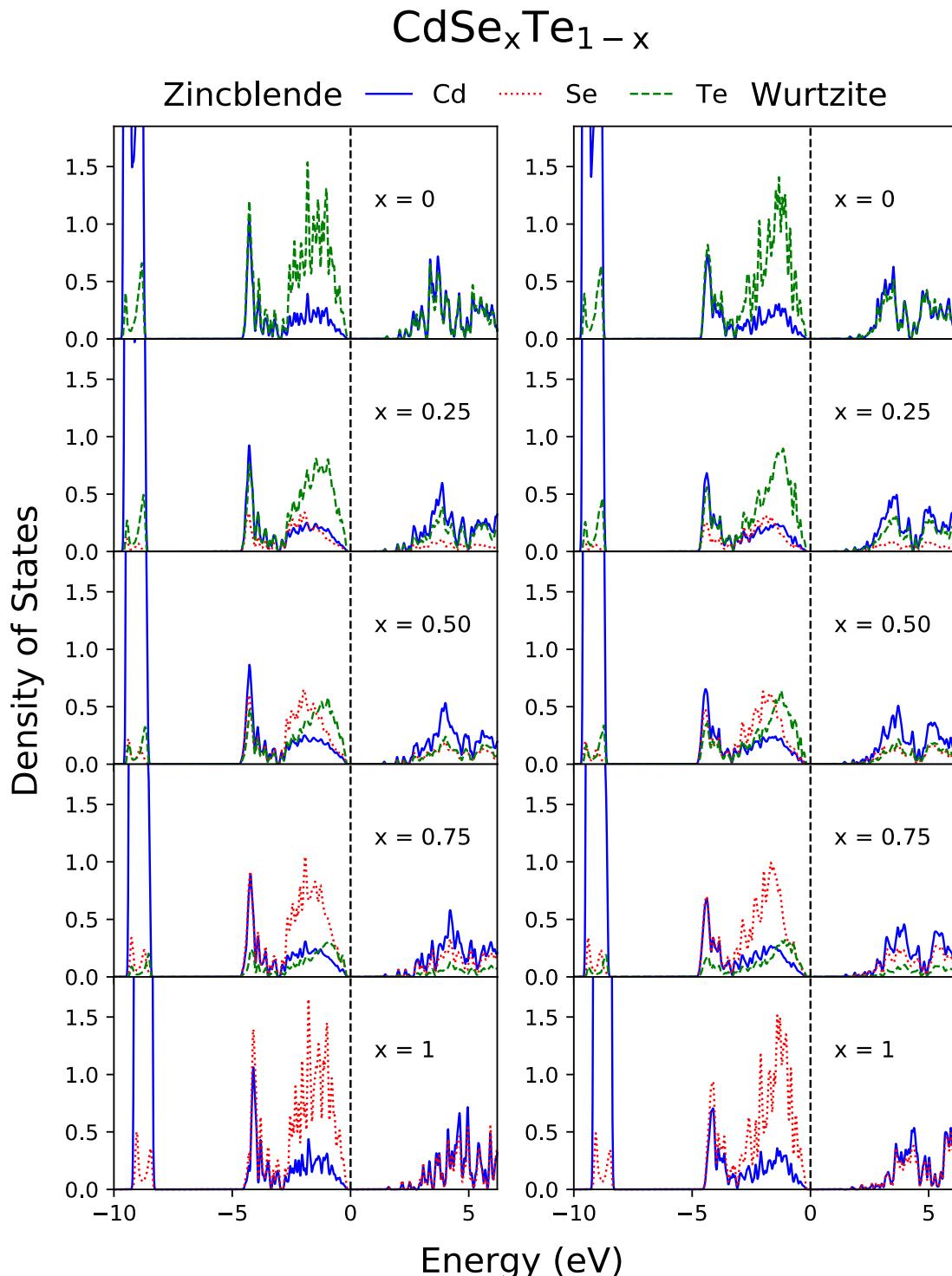
Structure	Zinc Blende		Wurtzite	
	Se	Te	Se	Te
Composition ( $x$ )				
0	N/A	0.52	N/A	0.51
0.25	0.72	0.52	0.72	0.51
0.50	0.72	0.51	0.72	0.52
0.75	0.72	0.51	0.72	0.51
1	0.70	N/A	0.71	N/A

**Table S4:** Average (DOS) effective masses of electrons and holes in zincblende and wurtzite  $\text{CdSe}_x\text{Te}_{1-x}$ . Units are in terms of the standard electron rest mass ( $m_0 \approx 9.11 \times 10^{-31} \text{ kg}$ ), i.e., the effective electron mass is  $m^* = m_e/m_0$  (and similar for holes,  $m_h$ ).

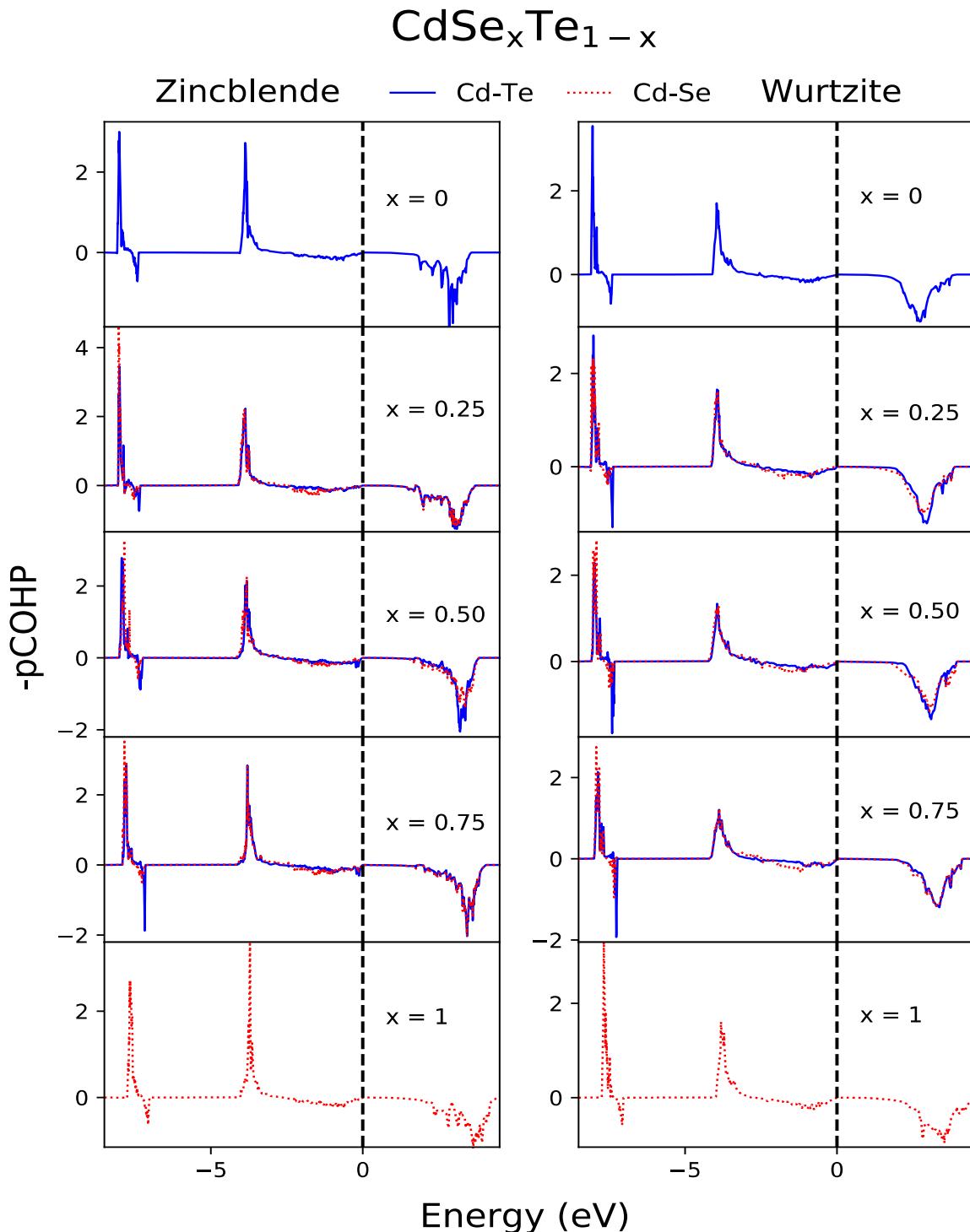
Material	Zincblende		Wurtzite		
	x	Electron	Hole	Electron	Hole
0.00		0.101	0.572	0.088	1.447
0.25		0.111	0.611	0.100	1.474
0.50		0.121	0.655	0.107	1.541
0.75		0.128	0.725	0.107	1.651
1.00		0.134	0.808	0.099	1.870



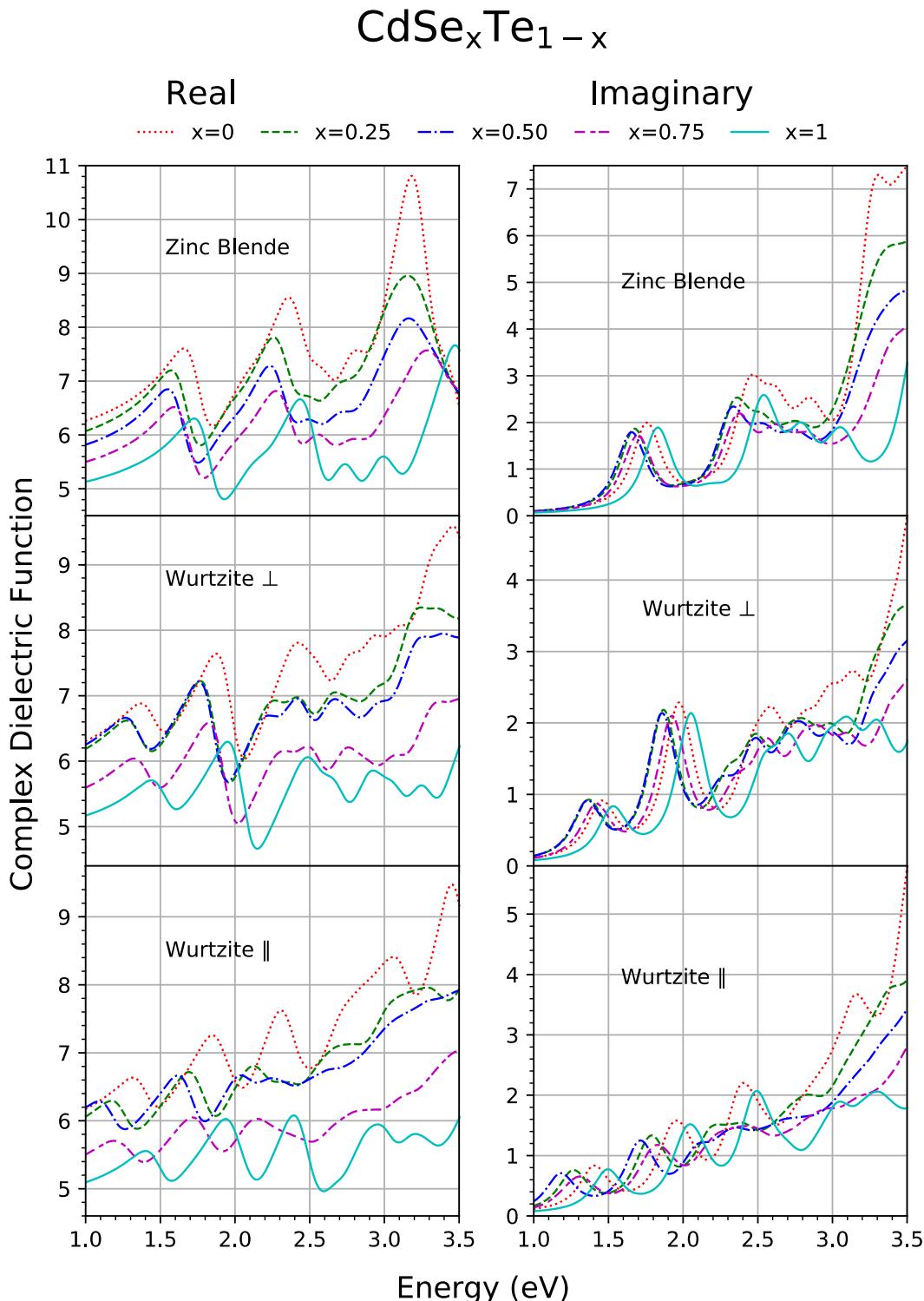
**Figure S1:** Box-and-whisker plots displaying the distribution of all unique bond lengths (Cd-Te, Cd-Se, Te-Te, Te-Se, Se-Se) within the disordered structures at intermediate concentrations ( $x = 0.25, 0.50, 0.75$ ) simulated using special quasirandom structures.



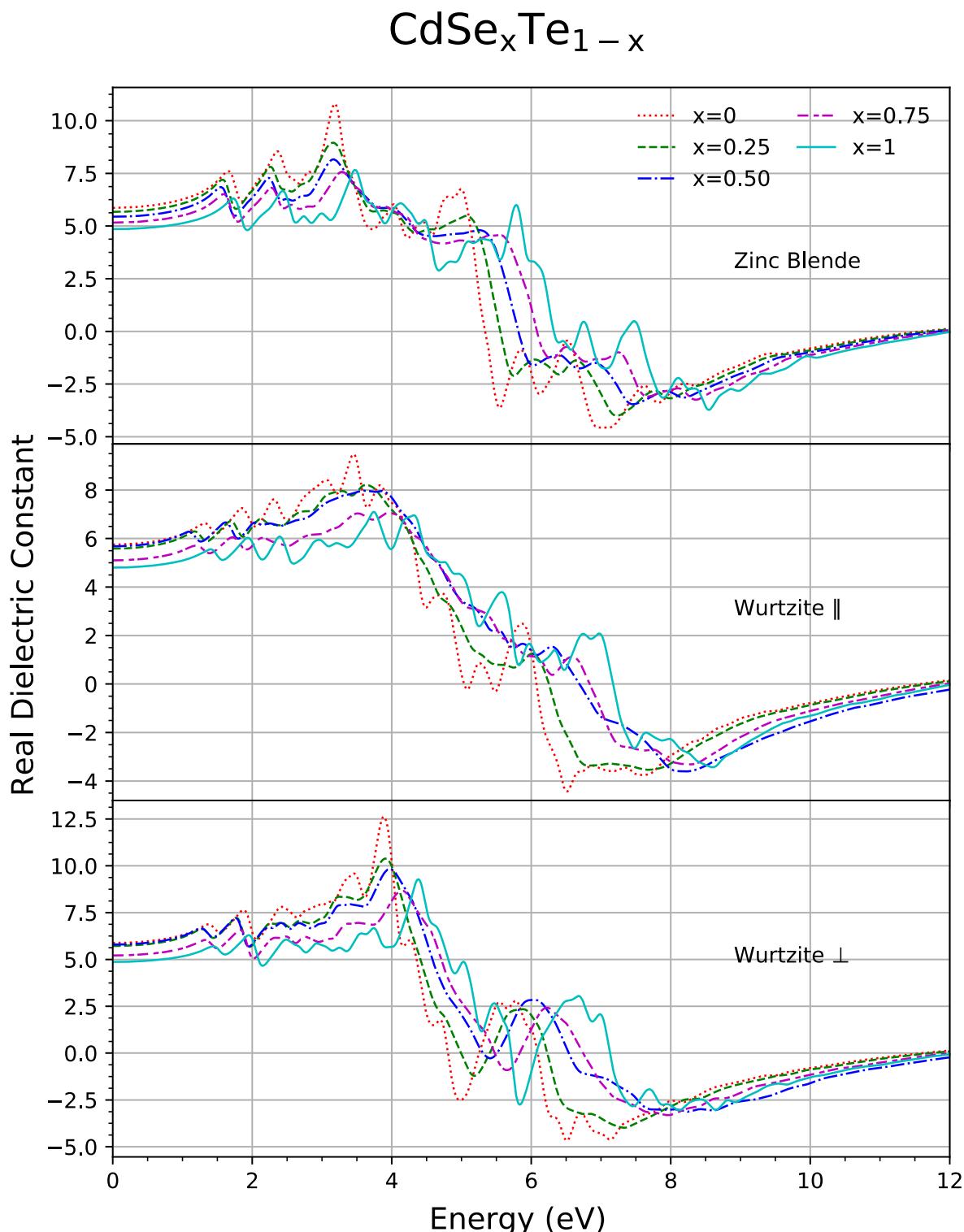
**Figure S2:** On-site electronic density of states per formula unit for each element for  $\text{CdSe}_x\text{Te}_{1-x}$  in the zincblende and wurtzite structures, calculated using the hybrid HSE06 functional. The Fermi energy is set to 0 eV.



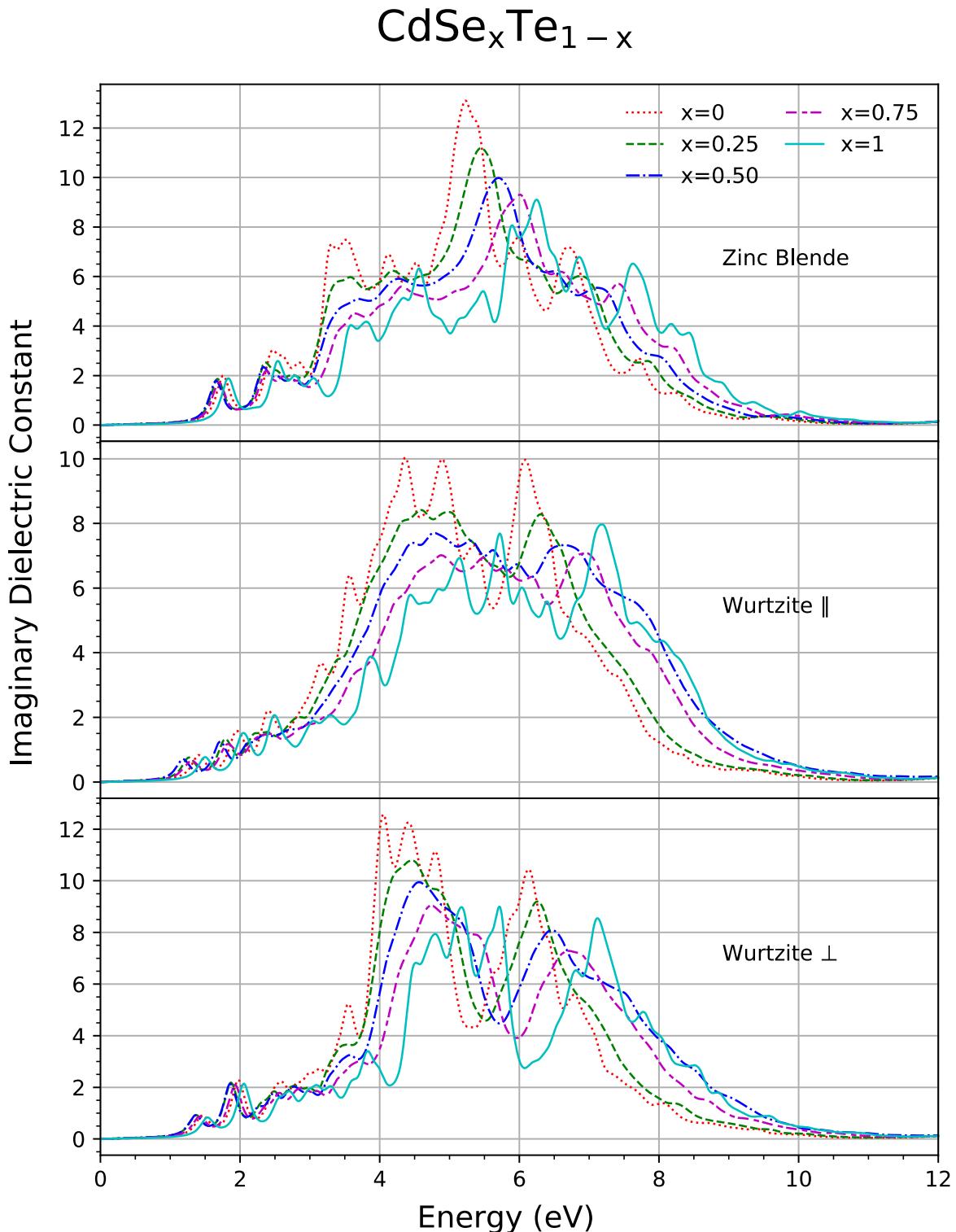
**Figure S3:** Projected Crystal Orbital Hamiltonian Populations (-pCOHP) of all nearest-neighbors in zincblende and wurtzite  $\text{CdSe}_x\text{Te}_{1-x}$ . Positive and negative values of -pCOHP correspond to bonding and antibonding respectively. Cd-Te and Cd-Se pairs are shown, whereas all other covalent interactions are negligible. The Fermi energy is set to 0 eV.



**Fig S4:** Complex dielectric functions for  $\text{CdSe}_x\text{Te}_{1-x}$  in the zincblende and wurtzite structures, calculated using the hybrid HSE06 functional. Photon energies in the visible-UV range are shown.



**Fig S5:** Variation of the real dielectric constants for  $\text{CdSe}_x\text{Te}_{1-x}$  in the zincblende and wurtzite structures, calculated using the hybrid HSE06 functional.



**Fig S6:** Variation of the imaginary dielectric constants for  $\text{CdSe}_x\text{Te}_{1-x}$  in the zincblende and wurtzite structures, calculated using the hybrid HSE06 functional.